

*B1*  
*C1*  
*cont'd*

an annular magnet array disposed within the chamber to form a stationary [substantially parallel] magnetic field that is substantially parallel to [at] the surface of the substrate support.

*B2*

5. (Twice Amended) The apparatus of claim [4] 3, wherein the target comprises a nickel/iron alloy.

6. (Twice Amended) [An] The apparatus of claim 1 [for depositing a magnetic film, comprising:] wherein the  
[a sputtering chamber containing a] target and [a] the substrate supporting surface are separated by a distance of at least about 50 mm [; and  
a magnet array disposed within the chamber to form a parallel magnetic field at the substrate supporting surface].

*B3*  
*sub*  
*62*

15. (Twice Amended) A method for depositing a magnetic film within a sputtering chamber containing a target and a substrate, comprising:  
sputtering the target onto a surface of the substrate at a pressure less than about 15 mTorr;  
collimating sputtering of the target with a grounded collimator disposed between the target and the substrate; and  
[providing] generating a [parallel] stationary magnetic field [at] that is substantially parallel to the surface of the substrate during sputtering using an annular magnet array disposed within the sputtering chamber.

*B4*

18. (Twice Amended) The method of claim [17] 16, wherein the target and the surface of the substrate are maintained at a distance of at least about 50 mm during sputtering.